12 A three-quadrant triacs, insulated, high commutation, high temperature

Rev. 02 — 11 March 2008

Product data sheet

1. Product profile

1.1 General description

Passivated, new generation, high commutation triacs in an internally insulated TO-220 plastic package.

1.2 Features

- Very high commutation performance
- Isolated mounting base
- High operating junction temperature
- High immunity to dV/dt
- 2500 V RMS isolation voltage

1.3 Applications

- Heating and cooking appliances
- High power motor control e.g. vacuum cleaners
- Solid state relays

- Non-linear rectifier-fed motor loads
- Electronic thermostats for heating and cooling loads

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BTA412Y-600B/C)}$
- $V_{DRM} \le 800 \text{ V (BTA412Y-800B/C)}$
- $I_{T(RMS)} \le 12 A$

- I_{GT} ≤ 50 mA (BTA412Y series B)
- I_{GT} \leq 35 mA (BTA412Y series C)
- $I_{TSM} \le 140 \text{ A (t = 20 ms)}$



2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------------------|--------------------|----------------|
| 1 | main terminal 1 (T1) | | . . |
| 2 | main terminal 2 (T2) | mb | T2—T1 |
| 3 | gate (G) | / U \ | sym051 |
| mb | mounting base; isolated | | |
| | | SOT78D (TO-220) | |

3. Ordering information

Table 2. Ordering information

| Type number | Package | | | | | |
|--------------|---------|---|--------------|--|--|--|
| | Name | Description | Version | | | |
| BTA412Y-600B | TO-220 | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; | nole; SOT78D | | | |
| BTA412Y-600C | | 3-lead TO-220 | | | | |
| BTA412Y-800B | | | | | | |
| BTA412Y-800C | | | | | | |

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|--|--------------|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | BTA412Y-600B; BTA412Y-600C | <u>[1]</u> - | 600 | V |
| | | BTA412Y-800B; BTA412Y-800C | - | 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_{mb} \le 116$ °C; see Figure 4 and 5 | - | 12 | Α |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3 | | | |
| | | t = 20 ms | - | 140 | А |
| | | t = 16.7 ms | - | 153 | А |
| l ² t | I ² t for fusing | $t_p = 10 \text{ ms}$ | - | 98 | A ² s |
| dl _T /dt | rate of rise of on-state current | $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$ | - | 100 | A/μs |
| I_{GM} | peak gate current | | - | 4 | А |
| P_GM | peak gate power | | - | 5 | W |

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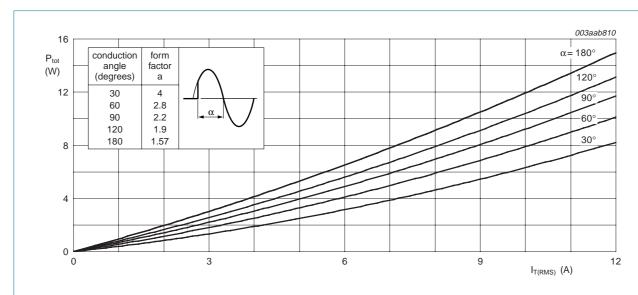
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Table 3. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

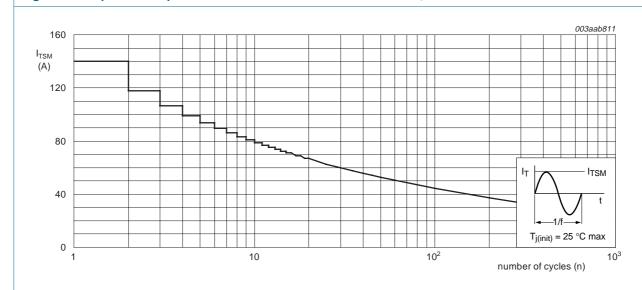
| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|-----------------------|-----|------|------|
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 1 | W |
| T _{stg} | storage temperature | | -40 | +150 | °C |
| T _j | junction temperature | | - | 150 | °C |

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.



 α = conduction angle

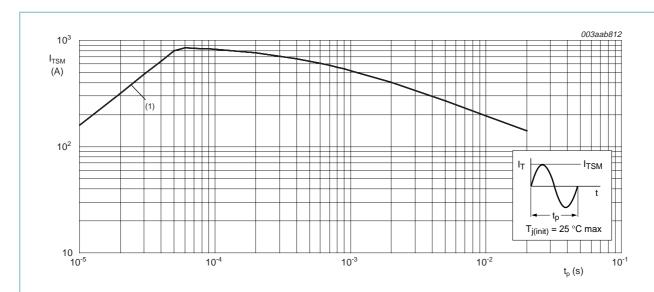
Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

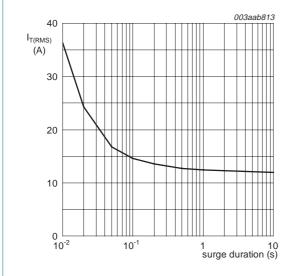
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 $t_p \le 20 \text{ ms}$

(1) dI_T/dt limit

Non-repetitive peak on-state current as a function of pulse duration; maximum values



f = 50 Hz

T_{mb} = 116 °C

Fig 4. RMS on-state current as a function of surge duration; maximum values

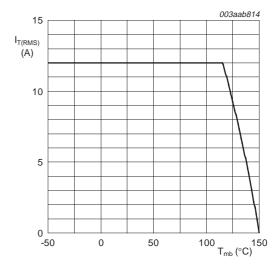


Fig 5. RMS on-state current as a function of mounting base temperature; maximum values

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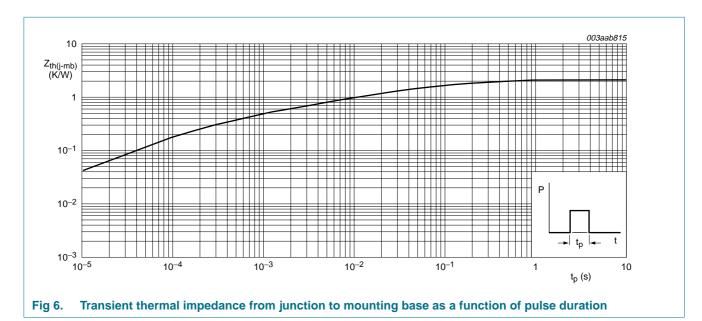
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5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|--------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; see Figure 6 | - | - | 2.1 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

| | • | | | | | |
|------------------------|-----------------------|---|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{isol(RMS)} | RMS isolation voltage | from all three terminals to external heatsink; f = 50 Hz to 60 Hz; sinusoidal waveform; RH ≤ 65 %; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | from pin 2 to external heatsink; f = 1 MHz | - | 10 | - | pF |

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Static characteristics

Static characteristics Table 6.

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

| Symbol | Parameter | Conditions | | BTA412Y-600B BTA412Y-800B | | | BTA412Y-600C BTA412Y-800C | | |
|---------------------------------|---|---|------|------------------------------|-----|------|------------------------------|-----|----|
| | | | Min | Тур | Max | Min | Тур | Max | |
| I _{GT} | gate trigger | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$ | | | | • | | | |
| | current | T2+ G+ | 2 | - | 50 | 2 | - | 35 | mA |
| | | T2+ G- | 2 | - | 50 | 2 | - | 35 | mA |
| | | T2- G- | 2 | - | 50 | 2 | - | 35 | mA |
| I _L latching current | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure } 10}{}$ | | | | | | | | |
| | | T2+ G+ | - | - | 60 | - | - | 50 | mΑ |
| | | T2+ G- | - | - | 90 | - | - | 60 | mΑ |
| | | T2- G- | - | - | 60 | - | - | 50 | mΑ |
| I _H | holding current | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure } 11}{}$ | - | - | 60 | - | - | 35 | mΑ |
| V_{T} | on-state voltage | I _T = 18 A; see <u>Figure 9</u> | - | 1.3 | 1.5 | - | 1.3 | 1.5 | V |
| V_{GT} | gate trigger | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 7}}{}$ | - | 8.0 | 1.5 | - | 0.8 | 1.5 | V |
| | voltage | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 ^{\circ}\text{C}$ | 0.25 | 0.4 | - | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$ | - | 0.1 | 0.5 | - | 0.1 | 0.5 | mA |
| | | $V_D = V_{DRM(max)}; T_j = 150 ^{\circ}C$ | - | 0.4 | 2 | - | 0.4 | 2 | mΑ |

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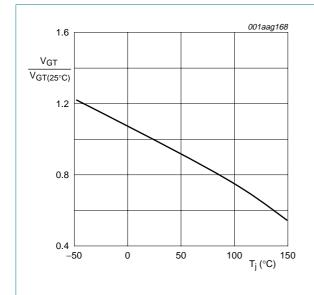
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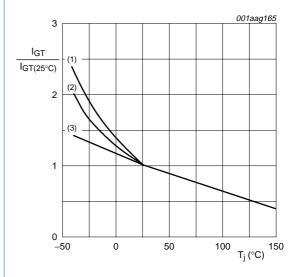
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8. Dynamic characteristics

Table 7. Dynamic characteristics

| Symbol | Parameter | Conditions | BTA412Y-600B BTA412Y-800B | | | BTA412Y-600C BTA412Y-800C | | | Unit |
|---|-------------------------------|---|------------------------------|-----|-----|------------------------------|-----|------|------|
| | | | Min | Тур | Max | Min | Тур | Max | |
| dV _D /dt rate of rise of off-state voltage | | $V_{DM} = 0.67 \times V_{DRM(max)}$; exponential waveform; gate open circuit | | | | | | | |
| | T _j = 125 °C | 1000 | - | - | 500 | - | - | V/µs | |
| | | T _j = 150 °C | 600 | - | - | 300 | - | - | V/µs |
| 00111 | rate of change of commutating | $V_{DM} = 400 \text{ V}; I_{T(RMS)} = 12 \text{ A}; \text{ without}$ snubber; gate open circuit | | | | | | | |
| | current | T _j = 125 °C | 20 | - | - | 15 | - | - | A/ms |
| | | T _j = 150 °C | 8 | - | - | 6 | - | - | A/ms |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$ | - | 2 | - | - | 2 | - | μs |





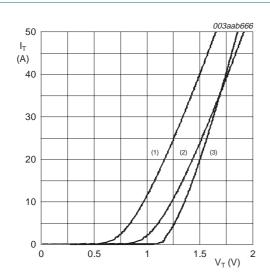
- (1) T2-G-
- (2) T2+ G-
- (3) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

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 $V_0 = 1.024 \text{ V}$

 $R_s = 0.021 \Omega$

(1) $T_j = 150 \,^{\circ}\text{C}$; typical values

(2) $T_i = 150 \,^{\circ}C$; maximum values

(3) $T_i = 25$ °C; maximum values

On-state current as a function of on-state Fig 9.

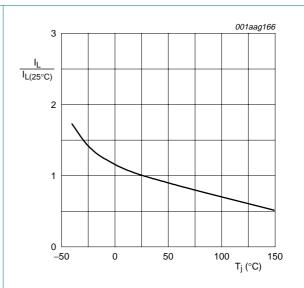


Fig 10. Normalized latching current as a function of junction temperature

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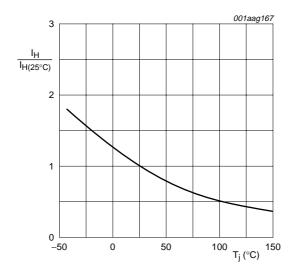


Fig 11. Normalized holding current as a function of junction temperature

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9. Package outline

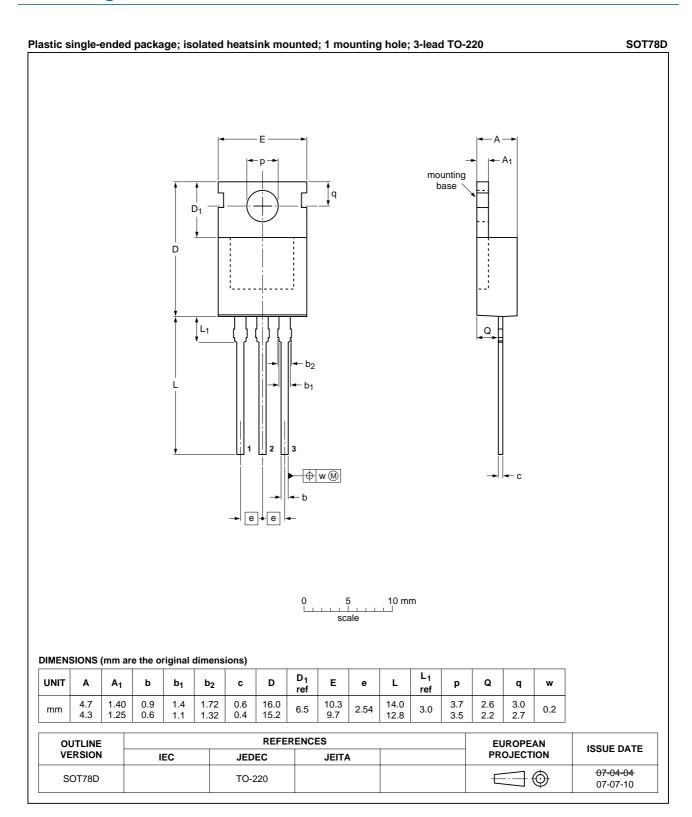


Fig 12. Package outline SOT78D (TO-220)

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10. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|---|--------------|--------------------|---------------|-------------------|--|
| BTA412Y_SER_B_C_2 | 20080311 | Product data sheet | - | BTA412Y_SER_B_C_1 | |
| Modifications: • Table 3 "Limiting values" uprated values for I _{GM} and P _{G(AV)} • Table 3 "Limiting values" updated I ² t condition symbol | | | | | |
| BTA412Y_SER_B_C_1 | 20071003 | Product data sheet | - | - | |

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11.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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